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# A Beginners' Guide to Scanning Electron Microscopy



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Anwar Ul-Hamid

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 Springer

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*To my wife*

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## Preface

The ability of the scanning electron microscope (SEM) to characterize materials has increased tremendously since its inception on a commercial basis at Cambridge, United Kingdom, in 1965. The tremendous prospects offered by this invention have been consistently built upon, thanks to steady advances in instrumentation and computer technology in the past few decades. Presently, surface morphology of materials ranging from biological, polymers, alloys to minerals, ceramics, and corrosion deposits is routinely studied from micrometer to nanometer scale. The SEM has emerged as a vital, powerful, and versatile tool in the advancement of modern day nanotechnology by contributing to the area of characterization of nanostructured materials. Its ease of use, typically prompt sample preparation and straightforward image interpretation combined with high resolution and high depth of field as well as the ability to undertake microchemical and crystallographic analysis, has made it one of the most popular techniques used for characterization. Presently, the SEM is being used by professionals with a diverse technical background, such as life science, materials science, engineering, forensics, and mineralogy, in various sectors of the government, industry, and academia.

A significant number of in-depth and specialized accounts of the scanning electron microscopy are available to interested readers. This book is meant to serve as a concise and brief guide to the practice of scanning electron microscopy. In this treatment, the material has been developed with the goal of providing an easily understood text for those SEM users who have little or no background in this area. It provides a solid introduction to the subject for the uninitiated. The instrumentation and working and image interpretation have been explained in a succinct practical guide to the SEM. The aim is to provide all useful information regarding SEM operation, applications, and sample preparation to the readers without them having to go through extensive reference material. Essential theory of specimen-beam interaction and image formation is treated in a manner that can be effortlessly comprehended by the readers. The SEM technique is described in simple terms to help operators and users of the SEM to get the best imaging results possible for their materials of interest. The capabilities and limitations of the SEM are also described to enable students, engineers, and materials scientists to identify and apply this technique for their work.

Necessary background to the SEM is developed in Chap. 1. Primary and secondary components of the instrument are introduced in Chap. 2. Basic concepts of electron beam-specimen interaction and contrast formation are described in Chap. 3. Chapter 4 elaborates on the mechanisms of image formation in the SEM. The working of the SEM is introduced, and the factors affecting the quality of images are discussed. Specialized SEM techniques are described briefly in Chap. 5. Chapters 6 and 7 elaborate the characteristics of x-rays and principles of EDS/WDS microchemical analysis, respectively. Chapter 8 includes sample preparation techniques used for various classes of materials. Images, illustrations, and photographs are used to explain concepts, provide information, and aid in data interpretation. The effect of various imaging conditions on the quality of images is described to help users get the best results for their materials of interest. The book is structured in a way that can help a novice find necessary information quickly.

The support of the King Fahd University of Petroleum & Minerals (KFUPM), Dhahran, through project number BW161001 is gratefully acknowledged. I am utterly indebted to Mr. Abuduliken Bake for drawing with great skill almost all of the illustrations appearing in this book. In addition, he has taken a number of SEM images and photographs. His help has been instrumental in the timely completion of the manuscript. I am also grateful to personnel working in various organizations who permitted the use of relevant material. I especially thank Mr. Tan Teck Siong from JEOL Asia Pte Ltd. for providing me with a number of wonderful images. I also extend my appreciation to my colleagues at the Materials Characterization Laboratory, Center for Engineering Research, KFUPM, for their continued support.

In the end, I am grateful to have been blessed with family and friends who make life truly worthwhile.

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# Contents

<b>1</b>	<b>Introduction</b>	1
1.1	What Is the SEM	1
1.2	Image Resolution in the SEM	1
1.3	Image Formation in the SEM	4
1.4	Information Obtained Using the SEM	4
1.5	Strengths and Limitations of the SEM	8
1.6	Brief History of the SEM Development	11
	References	14
<b>2</b>	<b>Components of the SEM</b>	15
2.1	Electron Column	15
2.1.1	Electron Gun	17
2.2	Thermionic Emission Electron Guns	20
2.2.1	Tungsten Filament Gun	22
2.2.2	Lanthanum Hexaboride (LaB <sub>6</sub> ) Emitter	28
2.3	Field Emission Electron Guns	30
2.3.1	Working Principle	30
2.3.2	Advantages/Drawbacks	31
2.3.3	Cold Field Emitter (Cold FEG)	32
2.3.4	Schottky Field Emitter	34
2.3.5	Recent Advances	36
2.4	Electromagnetic Lenses	37
2.4.1	Condenser Lens	39
2.4.2	Apertures	41
2.4.3	Objective Lens	41
2.4.4	Lens Aberrations	44
2.4.5	Scan Coils	52
2.4.6	Magnification	53
2.5	Specimen Chamber	56
2.5.1	Specimen Stage	56
2.5.2	Infrared Camera	58
2.6	Detectors	59
2.6.1	Everhart-Thornley Detector	59



2.6.2	Through-the-Lens (TTL) Detector . . . . .	64
2.6.3	Backscattered Electron Detector . . . . .	66
2.7	Miscellaneous Components . . . . .	71
2.7.1	Computer Control System . . . . .	71
2.7.2	Vacuum System . . . . .	72
2.7.3	High-Voltage Power Supply (HT Tank) . . . . .	74
2.7.4	Water Chiller . . . . .	74
2.7.5	Heater . . . . .	75
2.7.6	Anti-vibration Platform . . . . .	75
	References . . . . .	76
<b>3</b>	<b>Contrast Formation in the SEM . . . . .</b>	<b>77</b>
3.1	Image Formation . . . . .	77
3.1.1	Digital Imaging . . . . .	78
3.1.2	Relationship Between Picture Element and Pixel . . . . .	80
3.1.3	Signal-to-Noise Ratio (SNR) . . . . .	82
3.1.4	Contrast Formation . . . . .	85
3.2	Beam-Specimen Interaction . . . . .	86
3.2.1	Atom Model . . . . .	86
3.2.2	Elastic Scattering . . . . .	87
3.2.3	Inelastic Scattering . . . . .	88
3.2.4	Effect of Electron Scattering . . . . .	89
3.2.5	Interaction Volume . . . . .	90
3.2.6	Electron Range . . . . .	93
3.3	Origin of Backscattered and Secondary Electrons . . . . .	95
3.3.1	Origin of Backscattered Electrons (BSE) . . . . .	95
3.3.2	Origin of Secondary Electrons (SE) . . . . .	95
3.4	Types of Contrast . . . . .	97
3.4.1	Compositional or Atomic Number (Z) Contrast (Backscattered Electron Imaging) . . . . .	97
3.4.2	Topographic Contrast (Secondary Electron Imaging) . . . . .	113
	References . . . . .	127
<b>4</b>	<b>Imaging with the SEM . . . . .</b>	<b>129</b>
4.1	Resolution . . . . .	129
4.1.1	Criteria of Spatial Resolution Limit . . . . .	131
4.1.2	Imaging Parameters That Control the Spatial Resolution . . . . .	134
4.1.3	Guidelines for High-Resolution Imaging . . . . .	138
4.1.4	Factors that Limit Spatial Resolution . . . . .	140
4.2	Depth of Field . . . . .	141
4.3	Influence of Operational Parameters on SEM Images . . . . .	146
4.3.1	Effect of Accelerating Voltage (Beam Energy) . . . . .	146
4.3.2	Effect of Probe Current/Spot Size . . . . .	147
4.3.3	Effect of Working Distance . . . . .	151
4.3.4	Effect of Objective Aperture . . . . .	154

---

4.3.5	Effect of Specimen Tilt . . . . .	157
4.3.6	Effect of Incorrect Column Alignment . . . . .	159
4.4	Effects of Electron Beam on the Specimen Surface . . . . .	160
4.4.1	Specimen Charging . . . . .	160
4.4.2	Surface Contamination . . . . .	166
4.4.3	Beam Damage . . . . .	167
4.5	Influence of External Factors on SEM Imaging . . . . .	168
4.5.1	Electromagnetic Interference . . . . .	169
4.5.2	Floor Vibrations . . . . .	169
4.5.3	Poor Microscope Maintenance . . . . .	170
4.6	Summary of Operating Conditions and Their Effects . . . . .	171
4.7	SEM Operation . . . . .	172
4.7.1	Sample Handling . . . . .	173
4.7.2	Sample Insertion . . . . .	174
4.7.3	Image Acquisition . . . . .	175
4.7.4	Microscope Alignment . . . . .	176
4.7.5	Maintenance of the SEM . . . . .	177
4.8	Safety Requirements . . . . .	178
4.8.1	Radiation Safety . . . . .	178
4.8.2	Safe Handling of the SEM and Related Equipment . . . . .	179
4.8.3	Emergency . . . . .	179
	References . . . . .	180
<b>5</b>	<b>Specialized SEM Techniques . . . . .</b>	<b>181</b>
5.1	Imaging at Low Voltage . . . . .	181
5.1.1	Electron Energy Filtering . . . . .	182
5.1.2	Detector Technology . . . . .	183
5.1.3	Electron Beam Deceleration . . . . .	186
5.1.4	Recent Developments . . . . .	187
5.1.5	Applications . . . . .	189
5.2	Imaging at Low Vacuum . . . . .	189
5.2.1	Introduction . . . . .	189
5.2.2	Brief History . . . . .	190
5.2.3	Working Principle . . . . .	190
5.2.4	Detector for Low Vacuum Mode . . . . .	192
5.2.5	Gas Path Length . . . . .	193
5.2.6	Applications . . . . .	196
5.2.7	Latest Developments . . . . .	197
5.3	Focused Ion Beam (FIB) . . . . .	197
5.3.1	Introduction . . . . .	197
5.3.2	Instrumentation . . . . .	202
5.3.3	Ion-Solid Interactions . . . . .	204
5.3.4	Ion Imaging . . . . .	205
5.4	STEM-in-SEM . . . . .	206
5.4.1	Working Principle . . . . .	206

5.4.2	Advantages/Drawbacks . . . . .	208
5.4.3	Applications . . . . .	208
5.5	Electron Backscatter Diffraction (EBSD) . . . . .	210
5.5.1	Brief History . . . . .	211
5.5.2	Working Principle . . . . .	211
5.5.3	Experimental Setup . . . . .	213
5.5.4	Applications . . . . .	215
5.6	Electron Beam Lithography . . . . .	218
5.6.1	Introduction . . . . .	218
5.6.2	Experimental Set-Up . . . . .	219
5.6.3	Classification of E-beam Lithography Systems . . . . .	220
5.6.4	Working Principle . . . . .	221
5.6.5	Applications . . . . .	222
5.7	Electron Beam-Induced Deposition (EBID) . . . . .	224
5.7.1	Mechanism . . . . .	224
5.7.2	Advantages/Disadvantages of EBID . . . . .	225
5.7.3	Applications . . . . .	225
5.8	Cathodoluminescence . . . . .	226
5.8.1	Introduction . . . . .	226
5.8.2	Instrumentation . . . . .	227
5.8.3	Strengths and Limitations of SEM-CL . . . . .	229
5.8.4	Applications . . . . .	230
	References . . . . .	230
<b>6</b>	<b>Characteristics of X-Rays . . . . .</b>	<b>233</b>
6.1	Atom Model . . . . .	233
6.2	Production of X-Rays . . . . .	234
6.2.1	Characteristic X-Rays . . . . .	234
6.2.2	Continuous X-Rays . . . . .	236
6.2.3	Duane-Hunt Limit . . . . .	239
6.2.4	Kramer's Law . . . . .	239
6.2.5	Implication of Continuous X-Rays . . . . .	240
6.3	Orbital Transitions . . . . .	242
6.3.1	Nomenclature Used for Orbital Transition . . . . .	242
6.3.2	Energy of Orbital Transition . . . . .	242
6.3.3	Moseley's Law . . . . .	244
6.3.4	Critical Excitation Energy (Excitation Potential) . . . . .	244
6.3.5	Cross Section of Inner-Shell Ionization . . . . .	246
6.3.6	Overvoltage . . . . .	247
6.4	Properties of Emitted X-Rays . . . . .	249
6.4.1	Excited X-Ray Lines . . . . .	249
6.4.2	X-Ray Range . . . . .	250
6.4.3	X-Ray Spatial Resolution . . . . .	251
6.4.4	Depth Distribution Profile . . . . .	253

6.4.5	Relationship Between Depth Distribution $\phi(\rho z)$ and Mass Depth ( $\rho z$ ) . . . . .	254
6.4.6	X-Ray Absorption (Mass Absorption Coefficient) . . . . .	256
6.4.7	Secondary X-Ray Fluorescence . . . . .	261
	References . . . . .	263
<b>7</b>	<b>Microchemical Analysis in the SEM</b> . . . . .	<b>265</b>
7.1	Energy Dispersive X-Ray Spectroscopy (EDS) . . . . .	265
7.1.1	Working Principle . . . . .	267
7.1.2	Advantages/Drawbacks of EDS Detector . . . . .	272
7.2	Qualitative EDS Analysis . . . . .	272
7.2.1	Selection of Beam Voltage and Current . . . . .	273
7.2.2	Peak Acquisition . . . . .	273
7.2.3	Peak Identification . . . . .	273
7.2.4	Peak to Background Ratios . . . . .	275
7.2.5	Background Correction . . . . .	275
7.2.6	Duration of EDS Analysis . . . . .	275
7.2.7	Dead Time . . . . .	276
7.2.8	Resolution of EDS Detector . . . . .	276
7.2.9	Overlapping Peaks . . . . .	278
7.3	Artifacts in EDS Analysis . . . . .	278
7.3.1	Peak Distortion . . . . .	278
7.3.2	Peak Broadening . . . . .	278
7.3.3	Escape Peaks . . . . .	281
7.3.4	Sum Peaks . . . . .	282
7.3.5	The Internal Fluorescence Peak . . . . .	283
7.4	Display of EDS Information . . . . .	283
7.4.1	EDS Spectra . . . . .	284
7.4.2	X-Ray Maps . . . . .	284
7.4.3	Line Scans . . . . .	285
7.5	Quantitative EDS Analysis . . . . .	287
7.5.1	Introduction . . . . .	287
7.5.2	EDS with Standards . . . . .	289
7.5.3	Examples of ZAF Correction Method . . . . .	295
7.6	Standardless EDS Analysis . . . . .	296
7.6.1	First Principles Standardless Analysis . . . . .	298
7.6.2	Fitted Standards Standardless Analysis . . . . .	298
7.7	Low-Voltage EDS . . . . .	299
7.8	Minimum Detectability Limit (MDL) . . . . .	300
7.9	Wavelength Dispersive X-Ray Spectroscopy (WDS) . . . . .	300
7.9.1	Instrumentation . . . . .	300
7.9.2	Working Principle . . . . .	301
7.9.3	Analytical Crystals . . . . .	304
7.9.4	Detection of X-Rays . . . . .	304
7.9.5	Advantages/Drawbacks of WDS Technique . . . . .	305

7.9.6	Qualitative WDS Analysis . . . . .	306
	References . . . . .	306
<b>8</b>	<b>Sample Preparation . . . . .</b>	<b>309</b>
8.1	Metals, Alloys, and Ceramics . . . . .	309
8.1.1	Sampling . . . . .	309
8.1.2	Sectioning . . . . .	310
8.1.3	Cleaning . . . . .	310
8.1.4	Embedding and Mounting . . . . .	312
8.1.5	Grinding, Lapping, and Polishing . . . . .	312
8.1.6	Impregnation . . . . .	315
8.1.7	Etching . . . . .	315
8.1.8	Fixing . . . . .	316
8.1.9	Fracturing . . . . .	316
8.1.10	Coating Process . . . . .	318
8.1.11	Marking Specimens . . . . .	323
8.1.12	Specimen Handling and Storage . . . . .	323
8.2	Geological Materials . . . . .	324
8.2.1	Preliminary Preparation . . . . .	324
8.2.2	Cleaning . . . . .	324
8.2.3	Drying . . . . .	325
8.2.4	Impregnation . . . . .	325
8.2.5	Replicas and Casts . . . . .	326
8.2.6	Rock Sample Cutting . . . . .	326
8.2.7	Mounting the Sample into the SEM Holder . . . . .	326
8.2.8	Polishing . . . . .	327
8.2.9	Etching . . . . .	328
8.2.10	Coating . . . . .	328
8.3	Building Materials . . . . .	329
8.3.1	Preparation of Cement Paste, Mortar, and Concrete Samples . . . . .	329
8.3.2	Cutting and Grinding . . . . .	330
8.3.3	Polishing . . . . .	330
8.3.4	Impregnation Techniques . . . . .	331
8.3.5	Drying the Specimen . . . . .	332
8.3.6	Coating the Specimen . . . . .	332
8.3.7	Cleaning the Surface of the Specimen . . . . .	332
8.4	Polymers . . . . .	332
8.4.1	Types of Polymers . . . . .	333
8.4.2	Morphology of Polymers . . . . .	334
8.4.3	Problems Associated with the SEM of Polymers . . . . .	335
8.4.4	General Aspects in Polymers Preparation for SEM . . . . .	337
8.4.5	Sample Preparation Techniques for Polymers . . . . .	338

---

8.4.6	Devices Used in Microtomy . . . . .	339
8.4.7	Sample Preparation Procedure for Polymers . . . . .	340
8.5	Biological Materials . . . . .	348
8.5.1	Fixation . . . . .	349
8.5.2	Examples of Biological Sample Preparation . . . . .	351
	References . . . . .	358
	<b>Questions/Answers . . . . .</b>	<b>361</b>
	<b>Index . . . . .</b>	<b>397</b>

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## Abbreviations

BSE	Backscattered electron(s)
CAD	Computer-aided design
CCD	Charge-coupled device
CL	Cathodoluminescence
DBS detector	Distributed backscattered detector
E-beam lithography	Electron beam lithography
EBID	Electron beam-induced deposition
EBSD	Electron backscatter diffraction
EBSP	Electron backscatter pattern
EDS	Energy dispersive x-ray spectroscopy
EPMA	Electron probe microanalyzer
EsB detector	Energy selective Backscatter detector
ESEM	Environmental SEM
E-T detector	Everhart-Thornley detector
FEG	Field emission gun
FET	Field-effect transistor
FIB	Focused ion beam
FWHM	Full width at half maximum
FWTM	Full width at tenth maximum
GFIS	Gas field ion source
GPL	Gas path length
GSED	Gaseous secondary electron detector
GUI	Graphical user interface
HAADF	High-angle annular dark field
HSQ	Hydrogen silsequioxane
IBID	Ion beam-induced deposition
ICC	Incomplete charge collection
IPF map	Inverse pole figure map
LaB <sub>6</sub>	Lanthanum hexaboride
LABe detector	Low-angle backscattered electron detector
LG	Light guide
LMIS	Liquid metal ion source
LV	Low vacuum

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MCA	Multichannel x-ray analyzer
MCP	Microchannel plate
MDL	Minimum detectability limit
MFP	Mean free path
OM	Orientation map
PHA	Pulse-height analyzer
PLA	Pressure-limiting aperture
PMMA	Poly methyl methacrylate
PMT	Photomultiplier tube
Pre-Amp	Preamplifier
SACP	Selected area channeling pattern
SDD	Silicon drift detector
SE	Secondary electron(s)
SEM	Scanning electron microscope
Si(Li)	Lithium-drifted silicon
SNR	Signal-to-noise ratio
STEM	Scanning transmission electron microscope
t-EBSD	Transmission EBSD
TEM	Transmission electron microscope
TES	Transition edge x-ray sensor
TKD	Transmission Kikuchi diffraction
TTL	Through-the-lens
UED	Upper electron detector
UTW	Ultra-thin window
VPS	Volume plasma sources
WD	Working distance
WDS	Wavelength dispersive x-ray spectroscopy
XRD	X-ray diffractometer



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# Symbols List

$\sigma_A$	Standard deviation
$\left(\frac{\mu}{\rho}\right)$	Mass absorption coefficient
$C_i$	Mass fraction of element $i$
$n_B$	Number of incident beam electrons
$n_{SE}$	Number of secondary electrons
$p_g$	Pressure of the gas
$\sigma_g$	Total scattering cross section of gas molecule for electrons
$\Delta E$	Energy spread
$A$	Area, Atomic weight
$a, b, \text{ and } c$	Constants
$A, C$	Constants
$A_A$	Maximum intensity
$B$	Magnetic field
$C$	Contrast
$C_c$	Chromatic aberration coefficient
$C_i$ (standard)	Weight percent concentration of element $i$ in the standard
$C_i$ (unknown)	Weight percent concentration of element $i$ in unknown bulk specimen
$C_s$	Spherical aberration coefficient
$C_Z$	$Z$ contrast
$d$	Escape depth of SE
$d$	Lattice plane spacing
$d$	Resolution
$d$	Beam diameter
$d_0$	Crossover diameter
$d_A$	Diameter of astigmatism disc
$d_c$	Diameter of the chromatic aberration disc
$d_d$	Diameter of diffraction disc
$d_{opt}$	Optimum probe diameter
$d_p$	Probe diameter
$d_{p,min}$	Minimum probe size
$d_s$	Diameter of the spherical aberration disc

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$E$	Energy of the x-ray line
$e$	Electric charge in Coulomb
$E$	Kinetic energy
$E_0$	Incident beam energy
$E_A$	Average energy for the x-ray peak
$E_{\text{BSE}}$	Energy of the BSE
$E_c$	Critical energy of ionization
$E_{\text{exc}}$	Mean energy per excitation
$E_K$	Binding energy of K shell
$E_L$	Binding energy of L shell
$E_m$	Mean number of electron-hole pairs
$E_v$	Continuum x-ray photon energy at some point in the spectrum
$F$	Force
$h$	Planck's constant
$I$	Intensity of x-ray photons when leaving the specimen surface
$I$	Width of the intrinsic line of the detector
$I_0$	Original intensity of x-ray photons
$i_B$	Electron beam current entering the specimen
$i_b$	Beam current
$I_b$	Background intensity
$i_{\text{BSE}}$	Backscattered electron current moving out of the specimen
$I_{\text{cm}}$	Intensity of continuum x-ray
$i_e$	Emission current
$i_f$	Filament heating current
$I_i$ (standard)	Intensity of characteristic x-ray peak emanating from element $i$ in the standard
$I_i$ (unknown)	Intensity of characteristic x-ray peak emanating from element $i$ in unknown specimen
$i_p$	Probe current
$I_{p,\text{max}}$	Maximum probe current
IR	Infrared
$J$	Average loss in energy per event
$J_b$	Current density of electron beam
$J_c$	Current density of electron source
$k$	Boltzmann constant
LED	Light-emitting diode
$L_{\text{monitor}}$	Scan length on monitor
$L_{\text{picture element}}$	Length of picture element
$L_{\text{pixel}}$	Length of pixel
$L_{\text{specimen}}$	Scan length on specimen
$m$	Mass
$n$	Order of diffraction
$n$	Refractive index
$N$	Total number of atoms present in the irradiated volume

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$n$	Total number of ionization events
nm	Nanometer
$N_v$	Avogadro's number
$p$	Probability
$P$	Quality indicator of the electronics used
$Q$	Cross section of ionization
$R$	Detector's energy resolution
$R$	Electron range
$R$	Extent of backscattering
$r_s$	Skirt radius
$R_x$	X-ray range
$s$	Distance travelled by an electron in the specimen
$S$	Stopping power
$S_A$	Signal emitted by the feature A
$S_B$	Signal emitted by the feature B
$t$	Thickness of specimen travelled
$T$	Absolute temperature (K)
$t$	Acquisition time
$U$	Overvoltage
$\nu$	Electromagnetic radiation frequency
$v$	Velocity of the particle
$V_0$	Accelerating voltage
$W$	Work function
$X$	The equivalent FWHM related to incomplete charge collection and leakage current of the detector
$X_k$	Number of emitted x-ray photons
$Y$	X-ray peak intensity
$Z$	Atomic number
$\alpha$	Convergence angle of the beam
$\eta$	Backscatter coefficient
$\eta_B$	Number of incident beam electrons
$\eta_{BSE}$	Number of backscattered electrons
$\lambda_{SWL}$	Short wavelength limits
$\mu$	Absorption coefficient
$\rho$	Density
$\Phi$	Depth distribution function
$\varphi$	Work function
$\psi$	Take-off angle
$\omega$	Fluorescence yield
$\Omega$	Solid angle
$\alpha_{opt}$	Optimum convergence angle
$\beta$	Brightness of gun
$\beta_{max}$	Maximum brightness of gun
$\delta$	Secondary yield

$\lambda$	Wavelength, mean free path (escape depth of SE)
$\mu\text{m}$	Micron
$\theta$	Bragg angle of diffraction
$F$	Frame scan time
$q$	Detector efficiency